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Generated Document.

(11) Publication number: **05195183 A****PATENT ABSTRACTS OF JAPAN**(21) Application number: **04010016**(51) Int'l. Cl.: **C23C 2/14 C23C 2/08 C23C 2/10 H01L
21/288**(22) Application date: **23.01.92**

(30) Priority:

(43) Date of application
publication: **03.08.93**(84) Designated contracting
states:(71) Applicant: **MITSUBISHI ELECTRIC CORP**(72) Inventor: **SHIMODA HIROSHI**

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**(54) PRODUCTION FOR
SEMICONDUCTOR DEVICE****(57) Abstract:**

PURPOSE: To shorten a working hour which is long time (about 2 hours) in the conventional method, when producing an electrode for semiconductor element.

CONSTITUTION: A plating solution S is blown to a wafer 1, on which the semiconductor element is formed, and when current is applied between a cathode electrode 13 opposite to the wafer 1 and a current regulating anode electrode 8 to form the element electrode, high, low and reverse current are applied repeatedly from a current control type D.C. power source 10.

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